



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Edward Y. CHANG et al. Confirmation No: 4041
Appl. No. : 10/699,839
Filed : November 4, 2003
Title : GROWTH OF GaAs EPITAXIAL LAYERS ON Si
SUBSTRATE BY USING A NOVEL GeSi BUFFER LAYER

TC/A.U. : 2818
Examiner : M. H. C. Tran

Docket No.: CHAN3228/REF
Customer No: 23364

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to Rule 37 C.F.R. §§ 1.51(b), 1.56, 1.97 and 1.98, this Information Disclosure Statement is being submitted with the references in the above-identified patent application. A listing of these documents is submitted herewith on Form PTO-1449. The foreign references are herewith enclosed with an English language Abstract.

This Information Disclosure Statement is submitted prior to the mailing date of the first Official Action on the merits received by Applicants.

The Examiner is requested to acknowledge consideration of the information provided in this paper in accordance with prescribed procedures.

Respectfully submitted,

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Sheet 1 of 1

B/O Form PTO-1449		Atty/Court Number CHAN3228/REF	Serial Number 10/699,839
<p>U.S. Department of Commerce Patent and Trademark Office</p> <p>Information Disclosure Statement by Applicant</p>			
<p>Applicant Edward Y. CHANG et al.</p>			
Filing Date November 4, 2003		Group 2818	

U.S. Patent Documents

Foreign Patent Documents

Other Documents (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

Examiner _____ *Date Considered* _____

EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; Draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.